

Part Number: **ILD1011M1000HVA (Preliminary)**

Integra

TECHNOLOGIES, INC.

Avionics Band RF Power LDMOS FET

The high power transistor part number ILD1011M1000HVA is designed for Avionics systems operating at 1090 MHz. Operating at 50 μ s, 2% pulse conditions this LDMOS FET device supplies a minimum of 1000 watts of power at 1090 MHz. All devices are 100% screened for large signal RF parameters.



Silicon LDMOS FET

- High Power Gain
- Superior thermal stability

Class AB Operation

- Gate biased to $I_{DQ} = 60$ mA

Configuration

- Common Source

Gold Metal

- Maximum Reliability

Package

- Thermally enhanced
- Pb-free and RoHS-compliant

Epoxy Sealed Lid

- Gross Leak Qualified

RF Test Fixture

- Broadband
- Matched to 50 ohms
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

PRELIMINARY DATA

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Lot/Sn:	F (MHz)	Pi (W)	Id (A)	RL (dBc)	Po (W)	Nd (%)	Nd' (%)	G (dBc)
502304-11	1090	18	43.3	14	1108	51.2	55.1	17.89

Pulse format=50%us, 2% Idq=60mA, Vd=50V

Nd = Drain efficiency (including bias current)

Nd' = Drain efficiency (excluding bias current)

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	V_{DS}	--	92	V	--
BD	Gate-Source Voltage	V_{GS}	--	20	V	--
BD	Storage Temperature Range	T_{STG}	-55	+200	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	TBD	°C/W	$V_D=50V, I_{DQ}=60mA, T_F=25\pm 5^\circ C, P_{OUT}=1000W$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

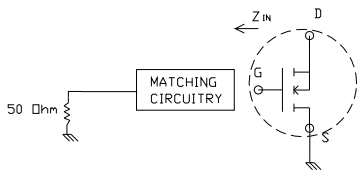
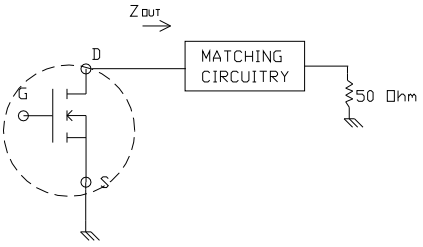
DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	BV_{DSS}	92	--	V	$I_D = 70mA, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Drain Leakage Current	I_{DSS}	--	48	μA	$V_{DS} = 50V, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Gate Threshold Voltage	V_{GSTH2}	2.75	5.25	V	$I_D = 100mA, V_{DS} = 5V, T_F = 25\pm 5^\circ C$
100%	Gate Leakage Current	I_{GSS}	--	1	μA	$V_{GS} = 5V, V_{DS} = 0V, T_F = 25\pm 5^\circ C$

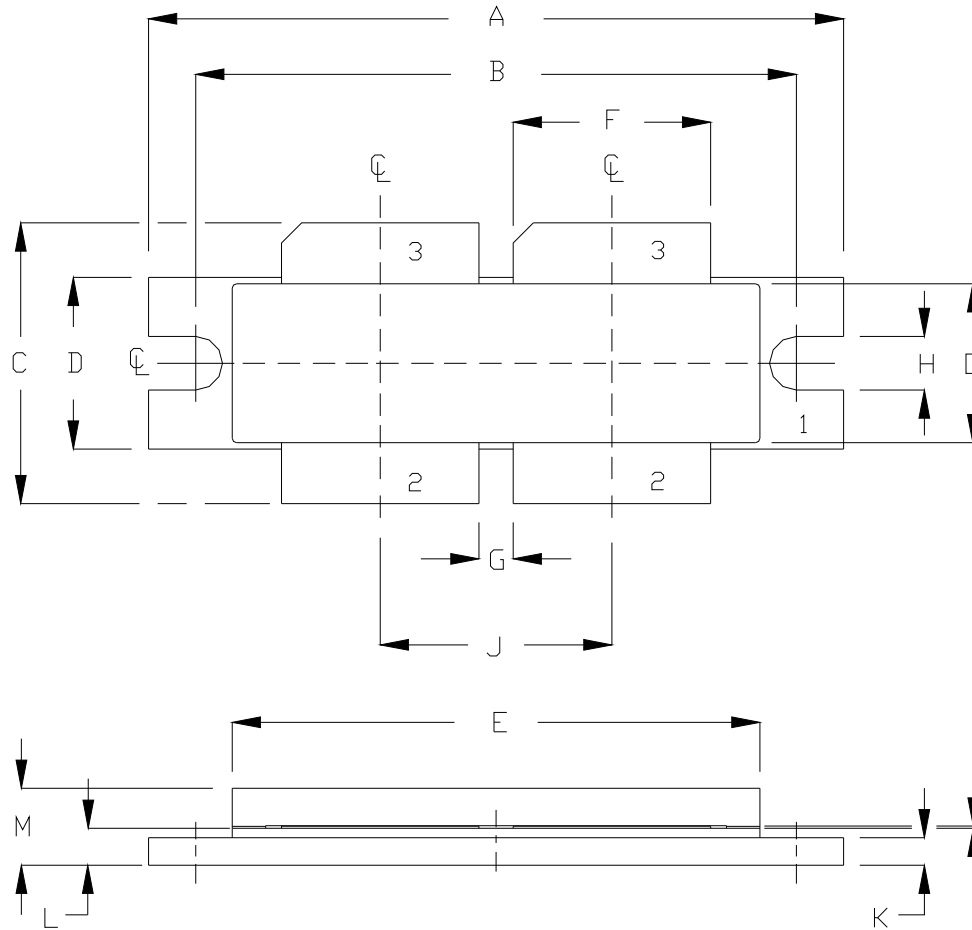
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	8	--	dB	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
BD	Maximum Overdrive	$P_{IN(MAX)}$	--	27	W	$V_{DD}=50V$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
100%	Power Gain	G_P	17.44	18.94	dB	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
100%	Output Power	P_{out}	1000	1410	W	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
100%	Drain Efficiency	N'_d	38	75	%	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
100%	Pulse Amplitude Droop	D	-0.5	+0.5	dB	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$.
100%	Stability into 2:1 VSWR	VSWR-S		2:1	--	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$. Rotate 2:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
BD	Load Mismatch Tolerance	LMT		20:1	--	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$. Rotate 20:1 output VSWR through 360° phase. Survival.
BD	Pulse Risetime	RT		60	ns	$V_{DD}=50V$, $P_{in}=18W$, Pulse=50 μ s, 2%, $T_F=25\pm 5^\circ C$, $F=F1$, $I_{DQ}=60mA$. Measure between 10% and 90% detected power points.
Note 1	F1 = 1090MHz.					
Note 2	Pulse format = 50 μ s, 2%					
Note 3	T_F = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
1090	0.28 + j0.80	0.5 + j0.21
Impedance Definition		

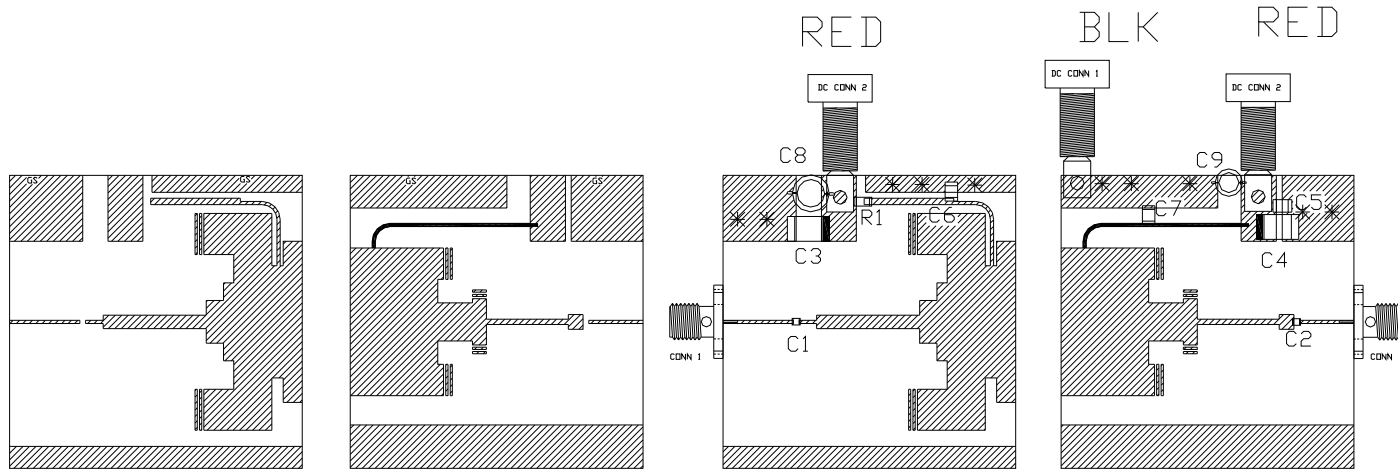
PACKAGE DIMENSIONAL OUTLINE DRAWING



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.27
B	1.395	1.405	35.43	35.69
C	0.634	0.674	16.10	17.12
D	0.395	0.405	10.03	10.29
E	1.219	1.241	30.96	31.52
F	0.455	0.465	11.56	11.81
G	0.075	0.085	1.90	2.16
H	0.120	0.130	3.05	3.30
J	0.535	0.545	13.59	13.84
K	0.059	0.069	14.99	17.53
L	0.081	0.091	2.06	2.31
M	0.164	0.194	4.16	4.93
N	0.004	0.007	0.10	0.18
□	0.354	0.364	8.99	9.24

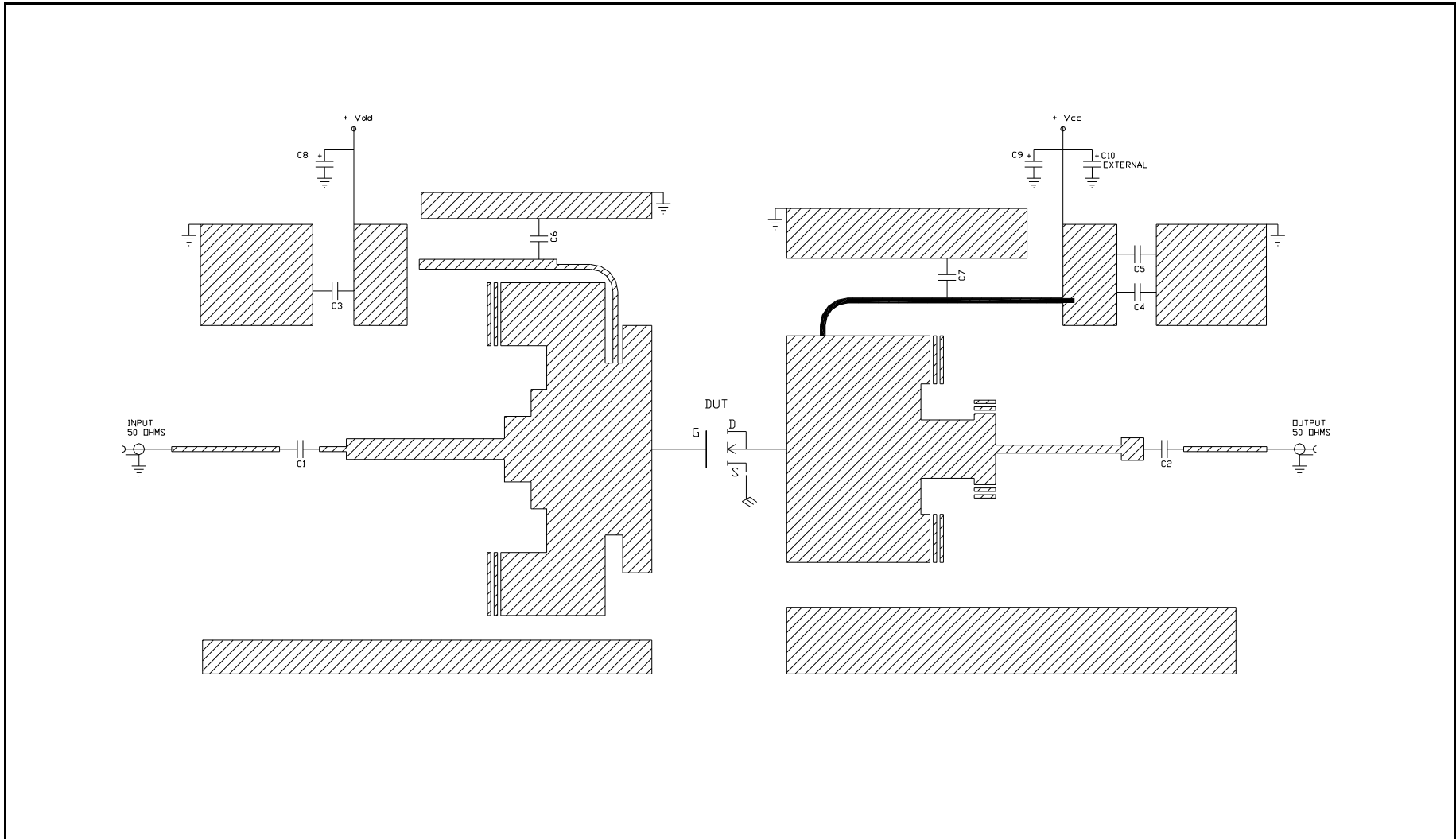
PIN SCHEDULE	
1	SOURCE
2	GATE
3	DRAIN

RF TEST FIXTURE – ASSEMBLY AND PARTS LIST



COMPONENT	DESCRIPTION
DUT	TRANSISTOR #ILD1011M1000HVA MOUNT HARD TO THE RIGHT
PC BOARD	RIGERS #R1 3010 10.2 025" 1oz. Cu
C1, C2	CHIP CAPACITOR ATC100A 39pf
C3, C4	TANTALUM AVX 4.7uF .50V ESR=0.3ohms
C5	CHIP CAPACITOR CERAMIC ATC100B 1000pf 250V
C6, C7	CHIP CAPACITOR ATC100B 47pf
C8, C9	ELECTROLYTIC CAPACITOR 68uF/763V
C10 (NOT SHOWN)	CAPACITOR 80V, 6800 uF
R1	RESISTOR 1206-300ohms
GS (10 PLACES)	GRDUND SHIM, COPPER, TH=0.001"
CDNN 1, CDNN 2	SMA CONNECTOR, DS #2052-5636-02
INPUT PC BOARD CARRIER	2 INCH BRASS-07 (2.0")
OUTPUT PC BOARD CARRIER	2 INCH BRASS-07 (2.0")
TRANSISTOR CARRIER	2 INCH COPPER-27
TRANSISTOR CLAMP	NUTTY CLAMP-09
ALUMINUM HEAT SINK	2 INCH HEATSINK-11
DC CDNN 1	BANANA JACK, BLACK
DC CDNN 2 (2 PLACES)	BANANA JACK, RED
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST USE CORNELL DUBILIER ALUMINUM FLAT PACK "MLP" SERIES OR SIMILAR FOR STORAGE CAPACITOR.

RF TEST FIXTURE – ELECTRICAL SCHEMATIC



DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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